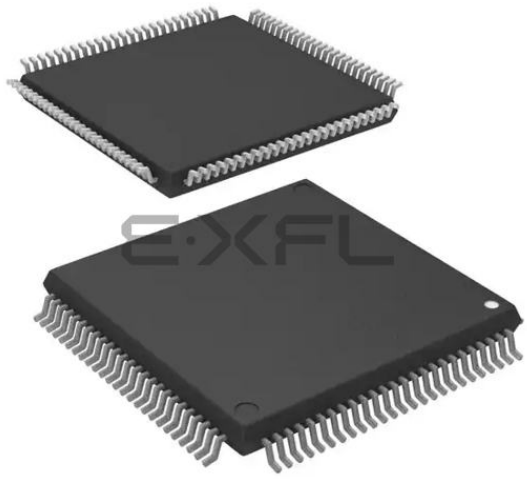
Renesas Electronics America Inc - R5F11MPGAFB#30 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, SPI, UART/USART
Peripherals	LCD, LVD, POR, PWM, WDT
Number of I/O	79
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	5.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 14x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f11mpgafb-30

○ ROM, RAM capacities

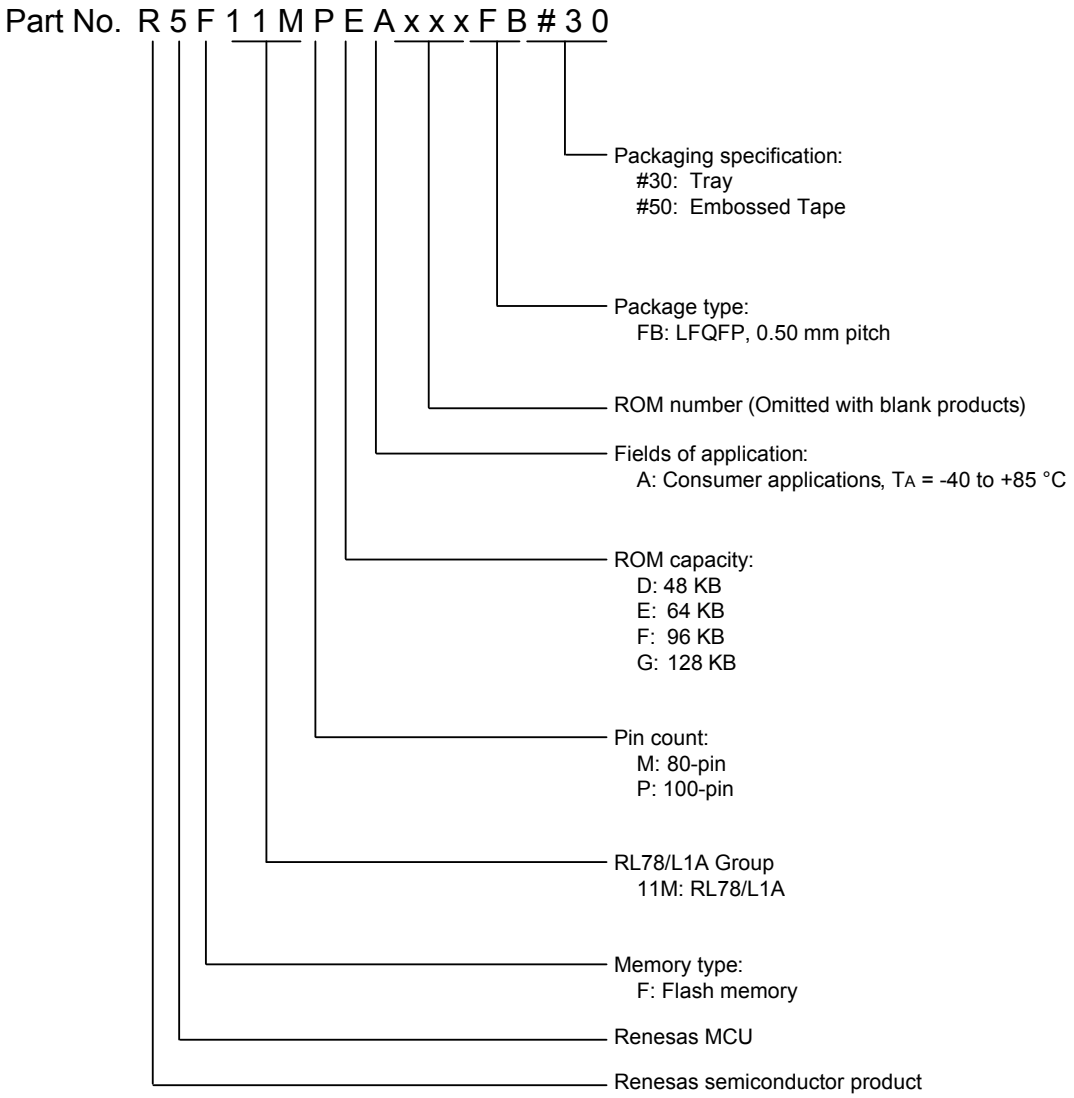
Products with USB

Flash ROM	Data Flash	RAM	RL78/L1A	
			80 pins	100 pins
128 KB	8 KB	5.5 KB	—	R5F11MPG
96 KB	8 KB	5.5 KB	R5F11MMF	R5F11MPF
64 KB	8 KB	5.5 KB	R5F11MME	R5F11MPE
48 KB	8 KB	5.5 KB	R5F11MMD	—

1.2 Ordering Information

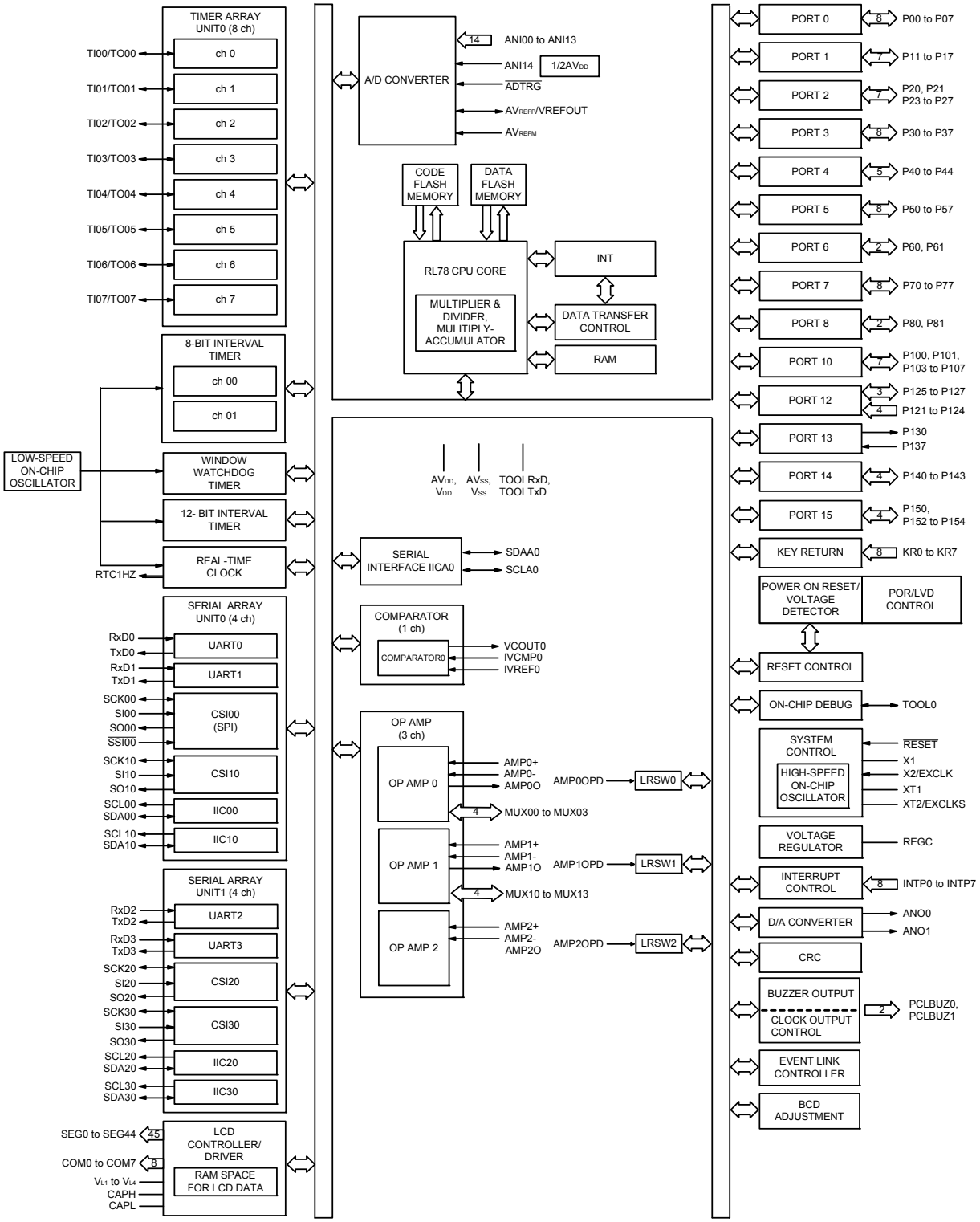
Pin Count	Package	Fields of Application	Orderable Part Number
80 pins	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	A	R5F11MMDAFB#30, R5F11MMEAFB#30, R5F111MFAFB#30 R5F11MMDAFB#50, R5F11MMEAFB#50, R5F11MMFAFB#50
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	A	R5F11MPEAFB#30, R5F11MPFAFB#30, R5F11MPGAFB#30 R5F11MPEAFB#50, R5F11MPFAFB#50, R5F11MPGAFB#50

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/L1A



Caution Orderable part numbers are current as of when this manual was published.
Please make sure to refer to the relevant product page on the Renesas website for the latest part numbers.

1.5.2 100-pin products



(2/2)

Item			80-pin	100-pin
			R5F11MMx (x = D to F)	R5F11MPx (x = E to G)
Clock output/buzzer output			2	2
			• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
12-bit resolution A/D converter			10 channels	14 channels
12-bit resolution D/A converter			2 channels	2 channels
VREFOUT (voltage reference)			2.5 V/2.048 V/1.8 V/1.5 V	
Operational amplifier			3 channels	3 channels
	AMPnO with analog MUX switch		2 channels (2 in-out/channel)	2 channels (4 in-out/channel)
Comparator			1 channel	1 channel
Serial interface			• CSI (SPI supported): 1 channel/UART (LIN-bus supported): 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel	
	I^2C bus		1 channel	1 channel
LCD controller/driver			Internal voltage boosting method, capacitor split method, and external resistance division method are switchable.	
	Segment signal output		32 (28) Note 1	45 (41) Note 1
	Common signal output		4 (8) Note 1	
Data transfer controller (DTC)			30 sources	30 sources
Event link controller (ELC)			Event input: 22, Event trigger output: 8	Event input: 22, Event trigger output: 8
Vectored interrupt sources		Internal	31	31
		External	9	9
Key interrupt			8	8
Reset			• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note 2 • Internal reset by RAM parity error • Internal reset by illegal-memory access	
Power-on-reset circuit			• Power-on-reset: 1.51 ±0.04 V • Power-down-reset: 1.50 ±0.04 V	
Voltage detector			• Rising edge: 1.88 V to 3.13 V (10 stages) • Falling edge: 1.84 V to 3.06 V (10 stages)	
On-chip debug function			Provided	
Power supply voltage			V_{DD} = 1.8 to 3.6 V	
Operating ambient temperature			T_A = -40 to +85 °C (A: Consumer applications)	

Note 1. The number in parentheses indicates the number of signal outputs when 8 coms are used.

Note 2. The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = -40 to +85 °C, 1.8 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, AV_{SS} = V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00 to P07, P11 to P17, P30 to P37, P40 to P44, P50 to P57, P70 to P77, P80, P81, P125 to P127, P130				-10.0 Note 2	mA
		Total of P00 to P07, P11 to P17, P30 to P37, P40 to P44, P50 to P57, P70 to P77, P80, P81, P125 to P127, P130 (When duty = 70% Note 3)	2.7 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V			-15.0	mA
			1.8 V ≤ AV_{DD} ≤ V_{DD} < 2.7 V			-7.0	mA
	I_{OH2}	Per pin for P20, P21, P23 to P27, P100, P101, P103 to P107, P140 to P143, P150, P152 to P154	1.8 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V			-0.1 Note 2	mA
		Total of P20, P21, P23 to P27, P100, P101, P103 to P107, P140 to P143, P150, P152 to P154 (When duty = 70% Note 3)	1.8 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V			-1.6	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin(IOH1), AV_{DD} pin(IOH2) to an output pin.

Note 2. However, do not exceed the total current value.

Note 3. Specification under conditions where the duty factor is 70%.
The output current value that has changed the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 50% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(50 × 0.01) = -14.0 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00-P02, P11, P12, P14, P35-P37, P40, P41, P43, P44, P80, P81 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85 °C, 1.8 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, AV_{SS} = V_{SS} = 0 V)

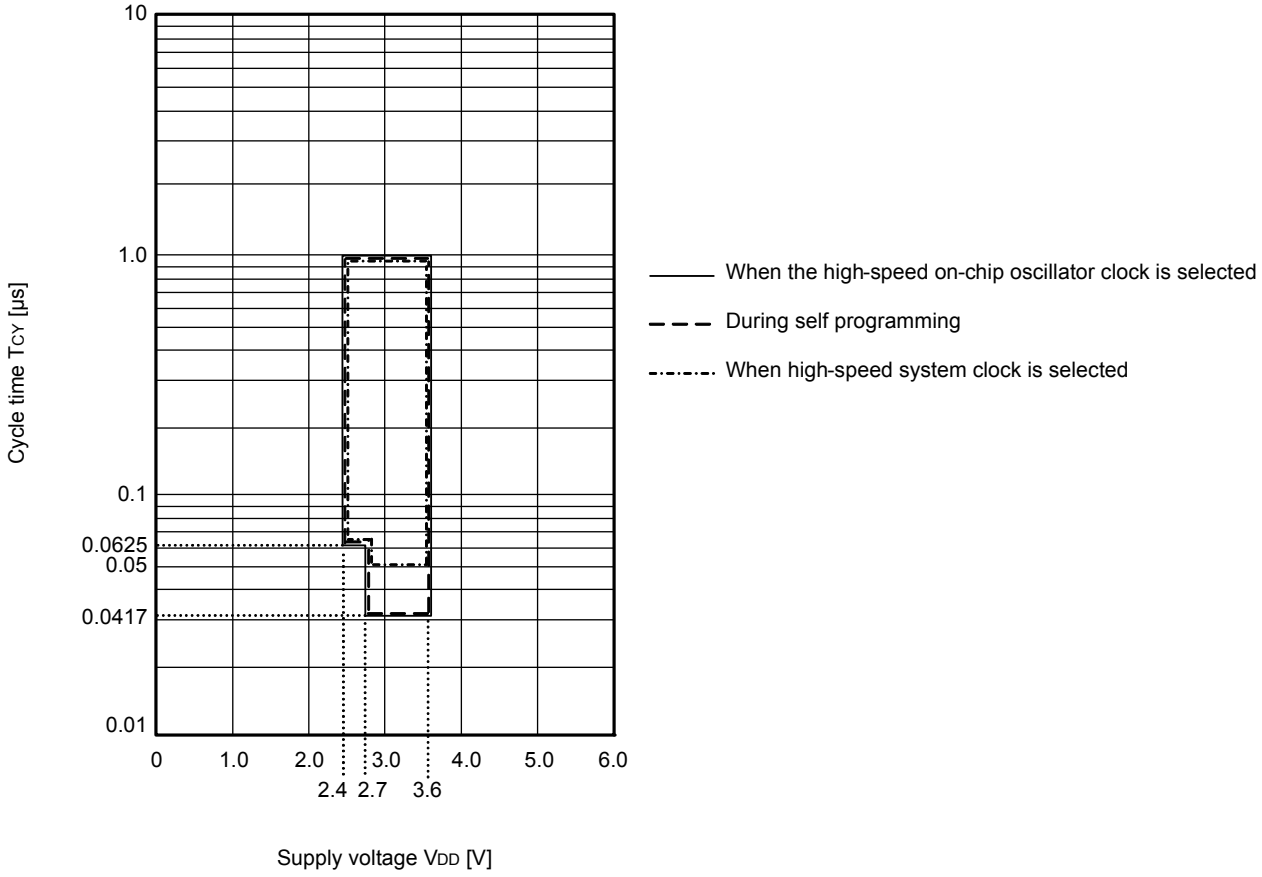
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	Port P00 to P07, P11 to P17, P30 to P37, P40 to P44, P50 to P57, P70 to P77, P80 to P81, P125 to P127	Normal input buffer	0.8 V_{DD}		V_{DD}	V
	V_{IH2}	For TTL mode supported ports	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	2.0		V_{DD}	V
			TTL input buffer 1.8 V ≤ V_{DD} < 3.3 V	1.50		V_{DD}	V
	V_{IH3}	P20, P21, P23 to P27, P100, P101, P103 to P107, P140 to P143, P150, P152 to P154		0.7 AV_{DD}		AV_{DD}	V
	V_{IH4}	P60, P61		0.7 V_{DD}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0.8 V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	Port P00 to P07, P11 to P17, P30 to P37, P40 to P44, P50 to P57, P70 to P77, P80 to P81, P125 to P127	Normal input buffer	0		0.2 V_{DD}	V
	V_{IL2}	For TTL mode supported ports	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	0		0.5	V
			TTL input buffer 1.8 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P20, P21, P23 to P27, P100, P101, P103 to P107, P140 to P143, P150, P152 to P154		0		0.3 AV_{DD}	V
	V_{IL4}	P60, P61		0		0.3 V_{DD}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		0.2 V_{DD}	V

Caution The maximum value of V_{IH} of pins P00 to P02, P11, P12, P14, P35 to P37, P40, P41. P43, P44, P80, P81 is V_{DD}, even in the N-ch open-drain mode.

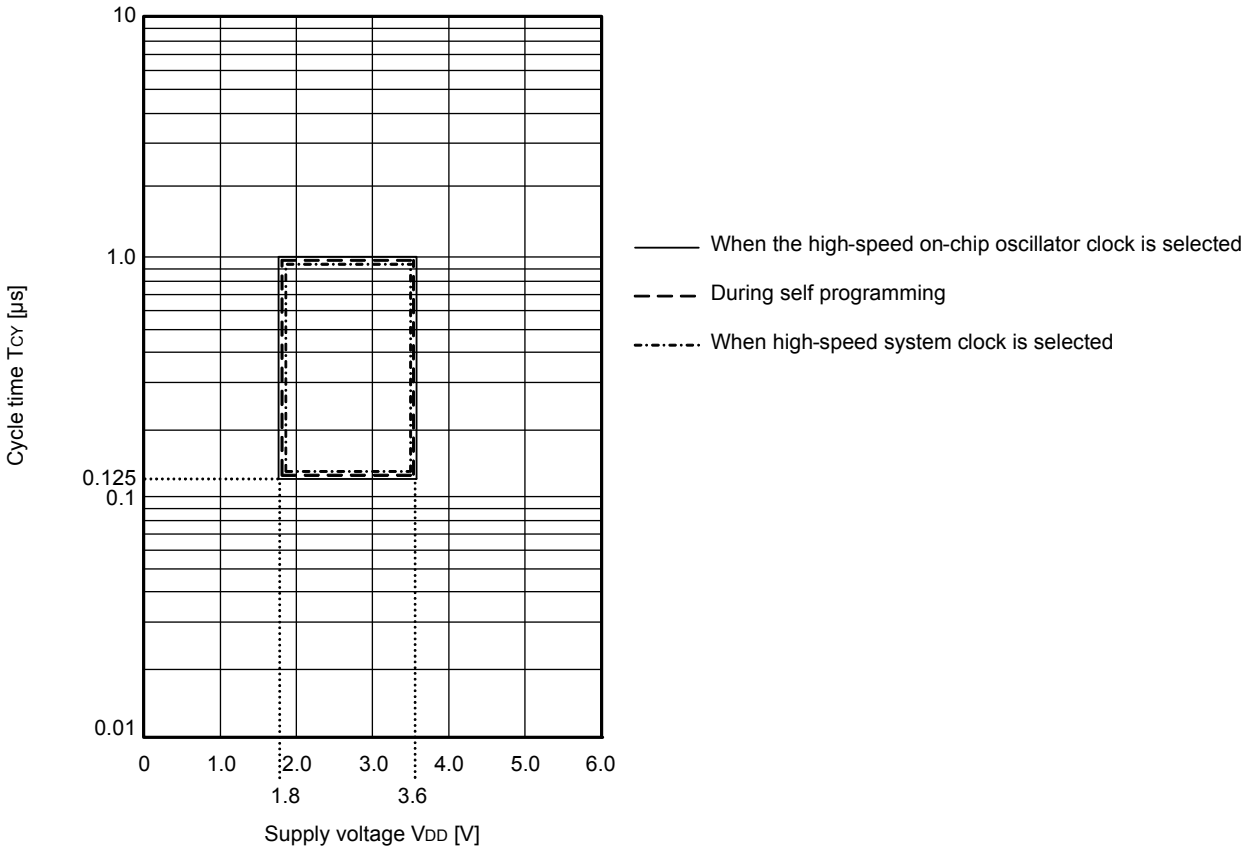
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Minimum Instruction Execution Time during Main System Clock Operation

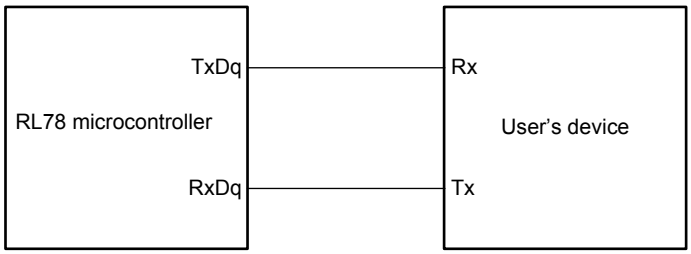
TCY vs VDD (HS (high-speed main) mode)



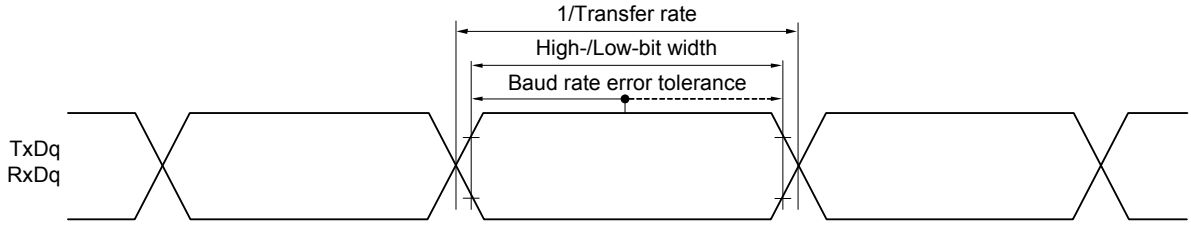
TCY vs VDD (LS (low-speed main) mode)



UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 4, 8)

Remark 2. fMCK: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85 °C, 2.7 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/2$	2.7 V ≤ V_{DD} ≤ 3.6 V	167		250		ns
SCKp high-/low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V		$t_{KCY1}/2$ - 10		$t_{KCY1}/2$ - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V		33		110		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 20 pF Note 4			10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

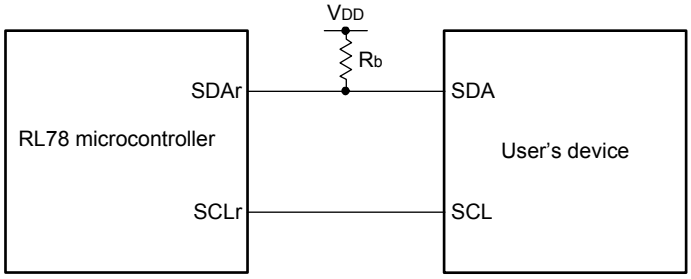
Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

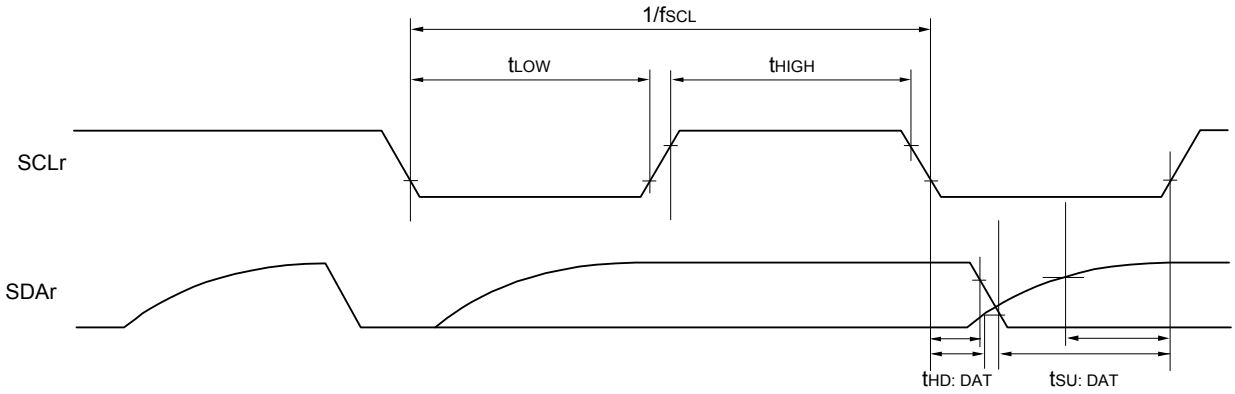
Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 4)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00))

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remark 1. Rb[Ω]: Communication line (SDAr) pull-up resistance, Cb[F]: Communication line (SCLr, SDAr) load capacitance

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM number (g = 0, 1, 3, 4, 8),
h: POM number (h = 0 to 3)

Remark 3. fMCK: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),
n: Channel number (n = 0, 2), mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5 V) (UART mode)

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)(2/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 2		transmission	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 2		1.2 Note 2	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Notes 3, 4		Notes 3, 4	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 5		0.43 Note 5	Mbps

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} ≤ 3.6 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. Use it with $V_{DD} \geq V_b$.

Note 4. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 1.8 V ≤ V_{DD} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 5. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(7) Communication at different potential (2.5 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85 °C, 2.7 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ	300		1150		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 10		t_{KCY1}/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ			130		130	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

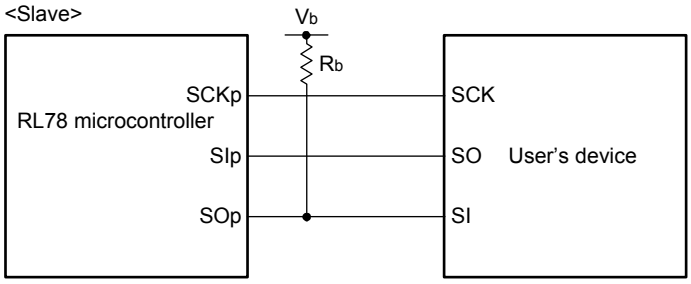
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0),
n: Channel number (n = 0), g: PIM and POM number (g = 4)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00))

CSI mode connection diagram (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 4, 8)

Remark 3. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02, 10, 12))

(10) Communication at different potential (1.8 V, 2.5 V) (simplified I^2C mode)

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		300 Note 1	kHz
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		400 Note 1		300 Note 1	kHz
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ		400 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1550		ns
		2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1150		1550		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1550		1550		ns
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	200		610		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	600		610		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	610		610		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 135 Note 3		1/f_{MCK} + 190 Note 3		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	355	0	355	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	0	405	0	405	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

Note 2. Use it with V_{DD} ≥ V_b.

Note 3. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

2.6.6 General purpose Operational amplifier characteristics

(T_A = -40 to +85 °C, 1.8 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, AV_{SS} = V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Circuit current	$I_{CC}1$	Low-power consumption mode			2	4	μA
	$I_{CC}2$	High-speed mode			140	280	μA
Common mode input range	V_{icm1}	Low-power consumption mode		0.2		AV_{DD}-0.5	V
	V_{icm2}	High-speed mode		0.3		AV_{DD}-0.6	V
Output voltage range	V_{o1}	Low-power consumption mode		0.1		AV_{DD}-0.1	V
	V_{o2}	High-speed mode		0.1		AV_{DD}-0.1	V
Input offset voltage	Fioff	3σ		-10		+10	mV
Open gain	A_V			60	120		dB
Gain-bandwidth (GB) product	GBW1	Low-power consumption mode			0.04		MHz
	GBW2	High-speed mode			1.7		MHz
Phase margin	PM	CL = 20 pF		50			deg
Gain margin	GM	CL = 20 pF		10			dB
Equivalent input noise	Vnoise1	f = 1 kHz	Low-power consumption mode		230		nV/√Hz
	Vnoise2	f = 10 kHz			200		nV/√Hz
	Vnoise3	f = 1 kHz	High-speed mode		90		nV/√Hz
	Vnoise4	f = 2 kHz			70		nV/√Hz
Power supply reduction ratio	PSRP				90		dB
Common mode signal reduction ratio	CMPR				90		dB
Operation stabilization wait time	Tstd1	CL = 20 pF	Low-power consumption mode			650	μs
	Tstd2	CL = 20 pF	High-speed mode			13	μs
Settling time	Tset1	CL = 20 pF	Low-power consumption mode			750	μs
	Tset2	CL = 20 pF	High-speed mode			13	μs
Slew rate	Tselw1	CL = 20 pF	Low-power consumption mode		0.02		V/μs
	Tselw2	CL = 20 pF	High-speed mode		1.1		V/μs
Load current	Iload1	Low-power consumption mode		-100		100	μA
	Iload2	High-speed mode		-100		100	μA
Load capacitance	CL					20	pF

LVD Detection Voltage of Interrupt & Reset Mode

(T_A = -40 to +85 °C, $V_{PDR} \leq V_{DD} \leq$ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDB0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 0, 1, falling reset voltage: 1.8 V		1.80	1.84	1.87	V
	V_{LVDB1}	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V
	V_{LVDB2}	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	V_{LVDB3}	LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	V_{LVDC0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 0, falling reset voltage: 2.4 V		2.40	2.45	2.50	V
	V_{LVDC1}	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	V_{LVDC2}	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	V_{LVDD0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 1, falling reset voltage: 2.7 V		2.70	2.75	2.81	V
	V_{LVDD1}	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDD2}	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V

2.6.11 Low-resistance switch

T_A = –40 to + 85°C, 1.8 V ≤ $AV_{DD} \leq V_{DD} \leq$ 3.6 V, $AV_{SS} = V_{SS}$ = 0 V

Parameter	Symbo	Conditions	MIN	TYP	MAX	Unit
ON resistance 1	Ron1	AMP0OPD, AMP1OPD Load current < 0.1 mA	—	16	50	Ω
ON resistance 2	Ron2	AMP2OPD Load current < 0.1 mA	—	10	30	
Load current	Icas	—	—	—	0.1	mA

[Reference value for design (not guaranteed)]

We can provide the design reference values for the low-resistance switch. Note, however, that these values are not guaranteed and can only be used as a reference when using this function. See below for details.

T_A = 0 to + 50°C, 2.0 V ≤ $AV_{DD} \leq V_{DD} \leq$ 3.6 V, $AV_{SS} = V_{SS}$ = 0 V

Parameter	Symbol	Conditions	MIN	TYP	MAX	Unit
ON resistance 1 Note 1, Note 2	Ron1	AMP0OPD, AMP1OPD Load current < 0.1 mA	—	—Note 3	26	Ω
ON resistance 2 Note 1, Note 2	Ron2	AMP2OPD Load current < 0.1 mA	—	—Note 3	15	
Load current	Icas	—	—	—	—Note 3	mA

Note 1. MAX. value is the average value ±3σ at normalized distribution.

Note 2. These values are the results of characteristic evaluation.

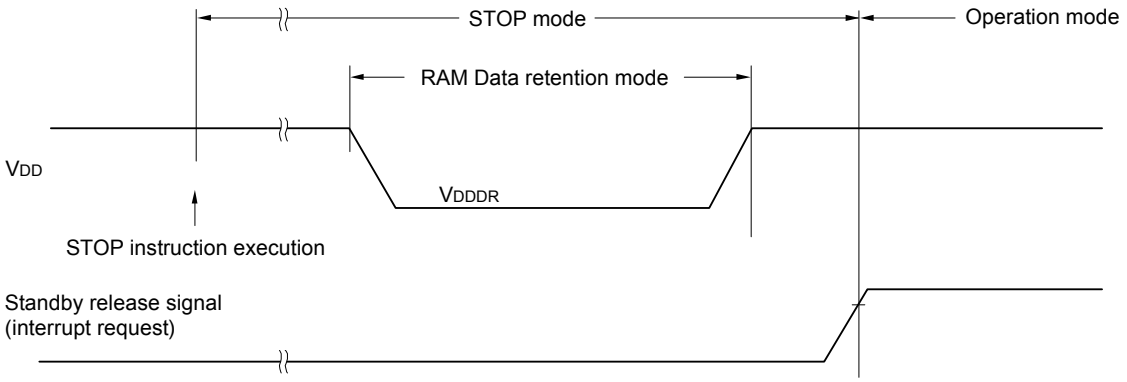
Note 3. The reference value is not available.

2.9 RAM data retention characteristics

(T_A = -40 to +85 °C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 Note		3.6	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



2.10 Flash Memory Programming Characteristics

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}	2.4 V ≤ V_{DD} ≤ 3.6 V		1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years	T_A = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year	T_A = 25°C		1,000,000		
		Retained for 5 years	T_A = 85°C	100,000			
		Retained for 20 years	T_A = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.11 Dedicated Flash Memory Programmer Communication (UART)

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

REVISION HISTORY	RL78/L1A Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Aug 12, 2016	—	First Edition issued

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California Eastern Laboratories, Inc.
4590 Patrick Henry Drive, Santa Clara, California 95054-1817, U.S.A.
Tel: +1-408-919-2500, Fax: +1-408-988-0279

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 1709, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100191, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852 2886-9022

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.
No.777C, 100 Feet Road, HAL II Stage, Indiranagar, Bangalore, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.
12F., 234 Teheran-ro, Gangnam-Gu, Seoul, 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141

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